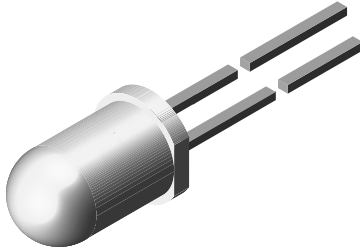


High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



94 8389

DESCRIPTION

TSHF6410 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Peak wavelength: $\lambda_p = 890$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 12$ MHz
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)

PRODUCT SUMMARY

| COMPONENT | I_e (mW/sr) | φ (deg) | λ_p (nm) | t_r (ns) |
|-----------|---------------|-----------------|------------------|------------|
| TSHF6410 | 70 | ± 22 | 890 | 30 |

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM |
|---------------|-----------|------------------------------|-------------------|
| TSHF6410 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
|-------------------------------------|---------------------------------------|------------|---------------|------------|
| Reverse voltage | | V_R | 5 | V |
| Forward current | | I_F | 100 | mA |
| Peak forward current | $t_p/T = 0.5, t_p = 100 \mu s$ | I_{FM} | 200 | mA |
| Surge forward current | $t_p = 100 \mu s$ | I_{FSM} | 1.5 | A |
| Power dissipation | | P_V | 160 | mW |
| Junction temperature | | T_j | 100 | $^\circ C$ |
| Operating temperature range | | T_{amb} | - 40 to + 85 | $^\circ C$ |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^\circ C$ |
| Soldering temperature | $t \leq 5$ s, 2 mm from case | T_{sd} | 260 | $^\circ C$ |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm soldered on PCB | R_{thJA} | 230 | K/W |

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

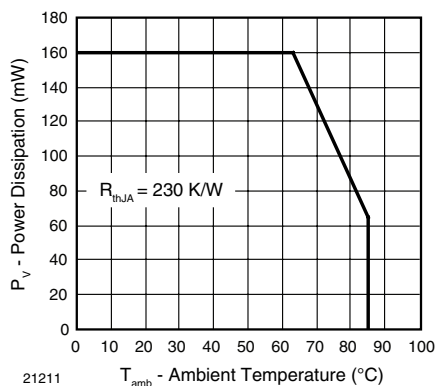


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

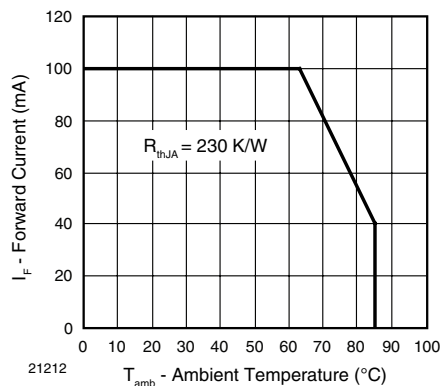


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|--|--|------------------|------|----------|------|---------------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | $I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$ | V_F | | 1.4 | 1.6 | V |
| | $I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$ | V_F | | 2.3 | | V |
| Temperature coefficient of V_F | $I_F = 1 \text{ mA}$ | TK_{V_F} | | - 1.8 | | mV/K |
| Reverse current | $V_R = 5 \text{ V}$ | I_R | | | 10 | μA |
| Junction capacitance | $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, $E = 0$ | C_j | | 125 | | pF |
| Radiant intensity | $I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$ | I_e | 45 | 70 | 135 | mW/sr |
| | $I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$ | I_e | | 700 | | mW/sr |
| Radiant power | $I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$ | ϕ_e | | 50 | | mW |
| Temperature coefficient of ϕ_e | $I_F = 100 \text{ mA}$ | TK_{ϕ_e} | | - 0.35 | | %/K |
| Angle of half intensity | | φ | | ± 22 | | deg |
| Peak wavelength | $I_F = 100 \text{ mA}$ | λ_p | | 890 | | nm |
| Spectral bandwidth | $I_F = 100 \text{ mA}$ | $\Delta\lambda$ | | 40 | | nm |
| Temperature coefficient of λ_p | $I_F = 100 \text{ mA}$ | TK_{λ_p} | | 0.25 | | nm/K |
| Rise time | $I_F = 100 \text{ mA}$ | t_r | | 30 | | ns |
| Fall time | $I_F = 100 \text{ mA}$ | t_f | | 30 | | ns |
| Cut-off frequency | $I_{DC} = 70 \text{ mA}$, $I_{AC} = 30 \text{ mA pp}$ | f_c | | 12 | | MHz |
| Virtual source diameter | | d | | 2.1 | | mm |

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

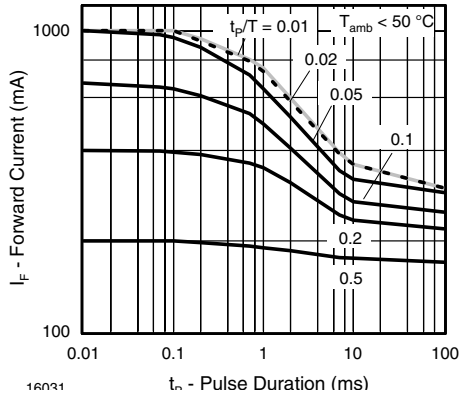


Fig. 3 - Pulse Forward Current vs. Pulse Duration

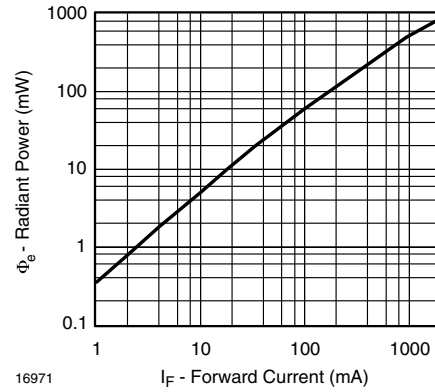


Fig. 6 - Radiant Power vs. Forward Current

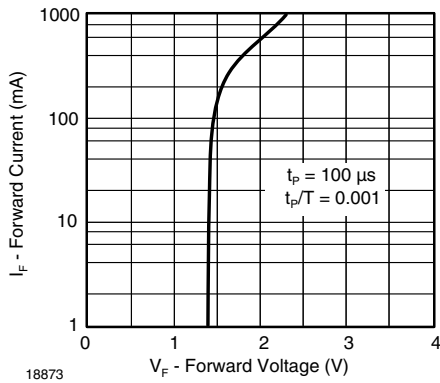


Fig. 4 - Forward Current vs. Forward Voltage

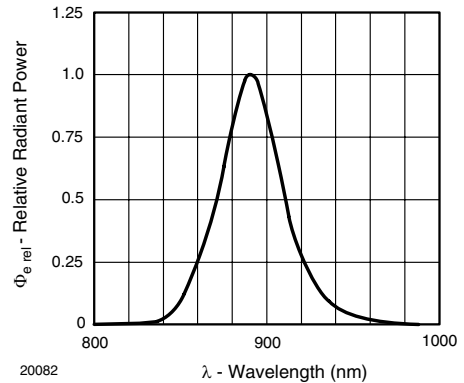


Fig. 7 - Relative Radiant Power vs. Wavelength

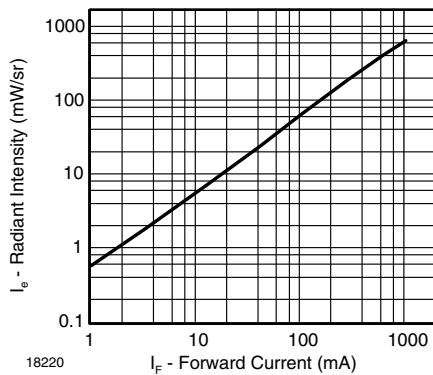


Fig. 5 - Radiant Intensity vs. Forward Current

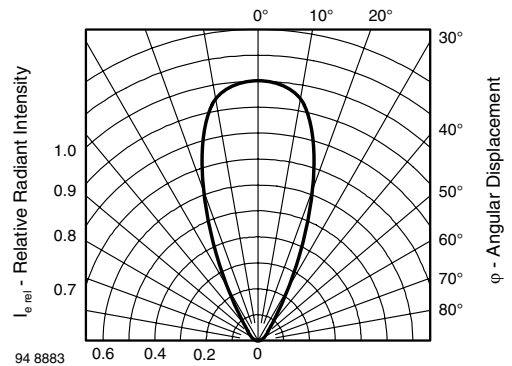


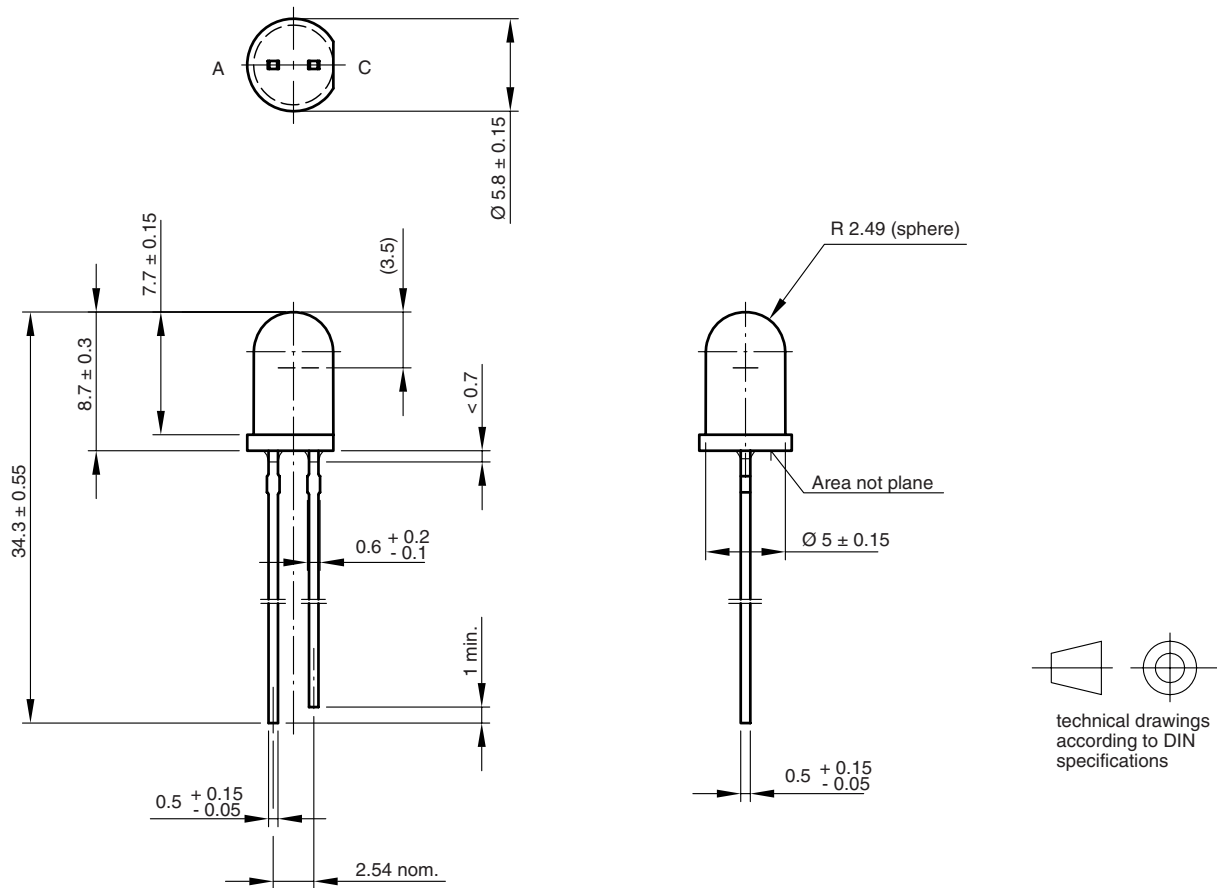
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

TSHF6410

Vishay Semiconductors High Speed Infrared Emitting Diode,
890 nm, GaAlAs Double Hetero



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5259.06-4
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19257



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